

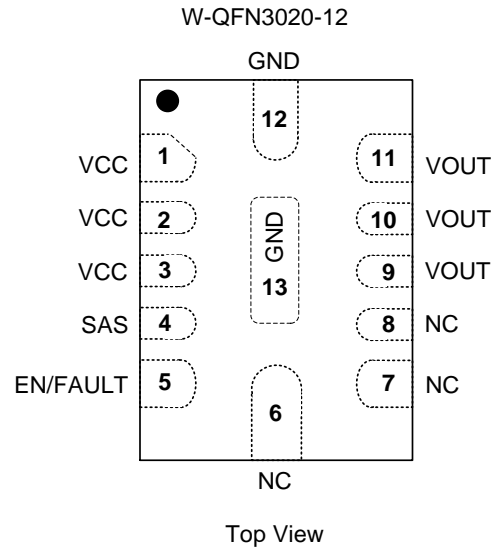
## Description

The eFuse is a 5V protection device with a bidirectional switch that incorporates input slew rate control to reduce input surge current and reverse current detection to prevent discharge to VCC from VOUT. The eFuse protection features include undervoltage protection, a fixed 2.5A current limit, trimmed fast response overvoltage protection and thermal shutdown. The EN/FAULT line is a tri-state bidirectional interface that can be used to disable the output by pulling the line low through an external open-drain device. If a thermal fault occurs, the voltage on the pin will go to an intermediate voltage indicating a fault and it can be connected to another device to cause simultaneous shutdown. The SAS pin is an ESD protected interface that allows direct external control of the eFuse. Driving the SAS pin high pulls the enable line low causing the eFuse to shut down and enter a low quiescent current state.

The integrated ISOFET latches off when the reverse current is detected. This can be reset only by triggering the undervoltage lockout, by EN/FAULT pin or when voltage on the output pin ( $V_{OUT}$ ) falls below the supply pin voltage ( $V_{CC}$ ) in the AP91350H.

The AP91350H is available in a standard Green W-QFN3020-12 package and is RoHS compliant.

## Pin Assignments



## Features

- SAS Disable
  - 2.1V Signal Disables the eFuse
  - ESD Compliant to 2kV HBM and 1kV CDM
- Integrated ISOFET That Latches Off When Reverse Current is Detected. Latch Off is Reset by
  - $V_{OUT}$  Falling Below  $V_{CC}$
  - UVLO Trigger
  - EN/FAULT Pin
- Input Tolerant of Continuous +12V
- 50m $\Omega$  Typical Total On-Resistance
- Fixed 2.5A Overcurrent Protection (OCP)
- Overvoltage Protection (OVP)
- Fixed 13ms +/- 20% Slew Rate Control (SRC)
- Overtemperature Protection (OTP)
- Undervoltage Lockout (UVLO)
- Thermally Efficient Low Profile Package, W-QFN3020-12
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.**  
<https://www.diodes.com/quality/product-definitions/>

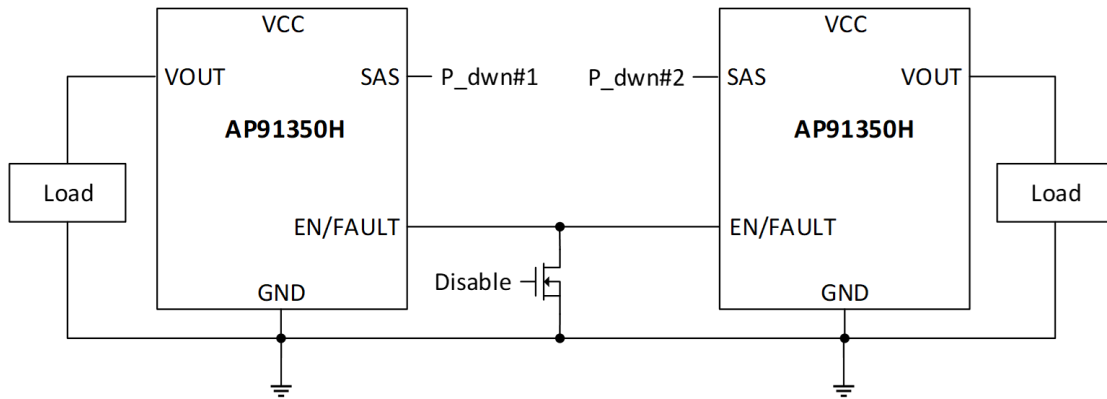
## Applications

- HDD drives
- SSD drives
- Mother board power management
- Printer load power management
- Fan drives

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

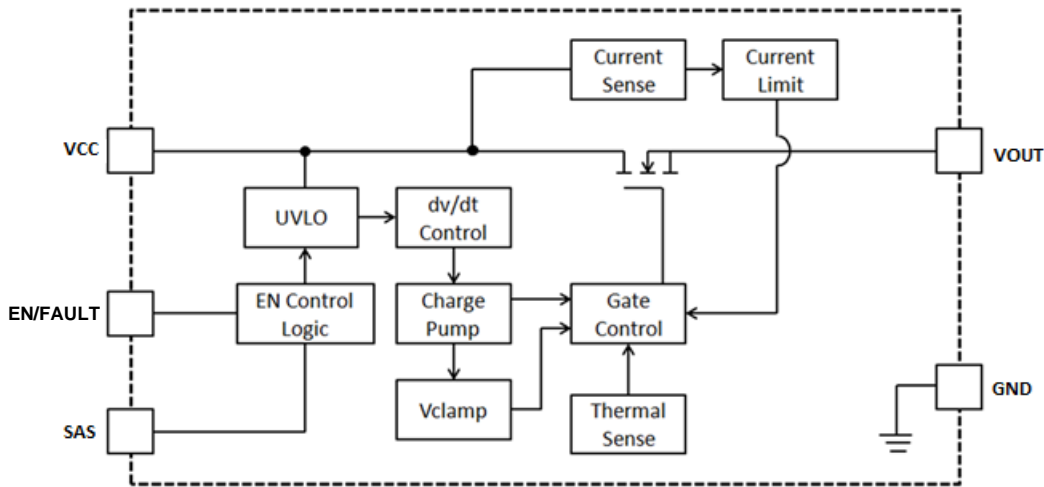
## Typical Applications Circuit



## Pin Descriptions

Pin Number	Pin Name	Description
1, 2, 3	VCC	Supply input, a minimum 10 $\mu$ F (Note 4) capacitor is needed to supply internal charge pump. The capacitor return should be connected directly to the GND pin.
4	SAS	SAS disable. When this pin is pulled high to a voltage greater than 2.1V, the eFuse is turned off.
5	EN/FAULT	The EN/FAULT pin is a tri-state, bidirectional interface. It can be used to enable or disable the output of the device by pulling it to ground using an open-drain device. If a thermal fault occurs, the voltage on this pin will go to an intermediate state to signal a monitoring circuit that the device is in thermal shutdown. It can also be connected to another device in this family to cause a simultaneous shutdown during thermal events.
6, 7, 8	NC	Do not connect on PCB, internally connected for production purpose.
9, 10, 11	VOUT	Output: eFuse controlled output; a 20 $\mu$ F capacitor is needed for overvoltage protection stability. The capacitor return should be connected directly to the GND pin.
12	GND	Ground
13	GND	Ground exposed pad

Note: 4. Minimum input capacitance is 10 $\mu$ F. Please refer to the *Input Capacitor Selection* in *Application Note* section.

**Functional Block Diagram**

**Absolute Maximum Ratings** (Note 5) (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Symbol	Parameter		Ratings	Unit
VCC	Input Voltage	Steady State	-0.3 to 16	V
		Transient (100ms)	-0.3 to 21	
EN/FAULT	Enable Voltage		-0.3 to 6	V
SAS	SAS Disable Voltage		-0.3 to 3.6	V
VOUT	VOUT Voltage		-0.3 to 7.0	V
ESD HBM	Human Body ESD Protection JESD22-A114		2000	V
ESD CDM	Charged Device Model ESD Protection JESD22-C101		1000	V
$T_{J(\text{Max})}$	Maximum Junction Temperature		+150	$^\circ\text{C}$
$T_{\text{ST}}$	Storage Temperature		-65 to +150	$^\circ\text{C}$
$P_D$	Power Dissipation ( $T_A = +25^\circ\text{C}$ )	W-QFN3020-12	1.3	W
$R_{\theta\text{JA}}$	Thermal Resistance, Junction to Ambient (0.5 square inch)	W-QFN3020-12 (Note 6)	40	$^\circ\text{C/W}$

- Notes:
- Stresses greater than those listed under *Absolute Maximum Ratings* can cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to *Absolute Maximum Ratings* for extended periods can affect device reliability.
  - For a device surface mounted on 25mm by 25mm by 1.6mm FR-4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady state condition.

**Recommended Operating Conditions** (All specifications are for  $-10^\circ\text{C} < T_A < +85^\circ\text{C}$ ,  $V_{\text{CC}} = 5\text{V}$ , unless otherwise noted.)

Symbol	Parameter	Min	Typ	Max	Unit
VCC	Input Voltage Range	3.6	—	12	V
$T_A$	Operating Ambient Temperature	-40	—	+85	$^\circ\text{C}$

**Electrical Characteristics** (Note 7) (All specifications are for  $-10^{\circ}\text{C} < T_A < +85^{\circ}\text{C}$ ,  $V_{CC} = 5\text{V}$ , unless otherwise noted.)

Symbol	Parameters	Conditions	Min	Typ	Max	Unit
<b>Supply Current</b>						
I <sub>Q</sub>	VCC Supply Current	EN = High, SAS = 0, I <sub>LOAD</sub> = 0A	—	—	300	μA
		Fault Latch off	—	100	—	μA
		EN = Low	—	—	100	μA
<b>Power FET</b>						
R <sub>DS(ON)</sub>	On-Resistance	T <sub>A</sub> = +25°C	—	50	65	mΩ
		T <sub>J</sub> = +80°C	—	95	—	mΩ
t <sub>ON-DLY</sub>	Turn-On Delay	Enable I <sub>D</sub> = 100mA, 1A Resistive Load	—	500	—	μs
I <sub>DC</sub>	Continuous Current	T <sub>A</sub> = +25°C, 0.5 Square inch Copper	—	2	—	A
I <sub>OFF</sub>	Off-State Leakage	V <sub>CC</sub> = 12V, EN = Low	—	—	1	μA
<b>Slew Rate Control</b>						
SRC	Slew Rate Control	EN to V <sub>OUT</sub> = 4.7V (Note 8)	10.4	13.0	15.6	ms
<b>Current Protection</b>						
I <sub>LIM</sub>	Current Limit	—	2.5	3.0	—	A
I <sub>SHORT</sub>	Short-Circuit Current	—	—	3.0	—	A
t <sub>LIM</sub>	Current Limit Response	—	5.5	—	40	μs
<b>Reverse Current Limit/Undervoltage Protection</b>						
I <sub>QREVERSE</sub>	Fast Reverse Current Limit	(Note 9)	0.9	—	1.7	A
t <sub>QREVERSE</sub>	Fast Reverse Current Limit Response Time	V <sub>CC</sub> dv/dt = -5V/1ms	5	—	10	μs
UVLO	Undervoltage Lockout	UVLO Rising	3.8	4.0	4.2	V
UVLO-hys	Undervoltage Hysteresis	—	—	0.3	—	V
—	Undervoltage Response	—	—	2.0	—	μs
<b>Overvoltage Protection</b>						
OVP	Overvoltage Clamping	—	5.5	6	6.25	V
t <sub>OVP</sub>	Overvoltage Response	C <sub>OUT</sub> = 20μF, dv/dt (V <sub>CC</sub> ) = 0.5V/μs V <sub>OUT</sub> < 6.5V	—	20	40	μs
<b>Thermal Protection</b>						
THSD	Shutdown Temperature	—	+130	+150	+200	°C
<b>Enable/Fault</b>						
V <sub>L</sub>	Logic Level Low	Output Disabled (Note 8)	0.35	—	0.8	V
V <sub>M</sub>	Logic Level Mid	Thermal Fault, Output Disabled (Note 8)	0.9	—	1.95	V
V <sub>H</sub>	Logic Level High	Output Enabled	2.1	—	3.3	V
V <sub>MAX</sub>	Maximum High State	—	3.4	—	5.2	V
I <sub>L</sub>	Logic Low Sink Current	EN = 0V	—	-12	-20	μA
I <sub>H</sub>	Logic Level High	EN = 3.3V	—	—	1	μA
FAN	Fan Out	—	—	—	3	Units

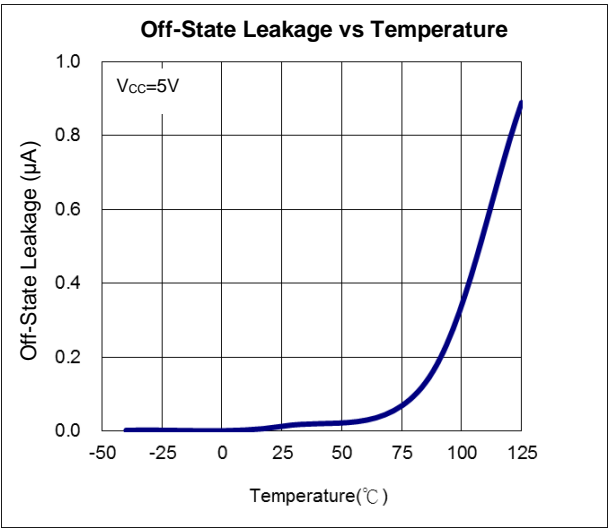
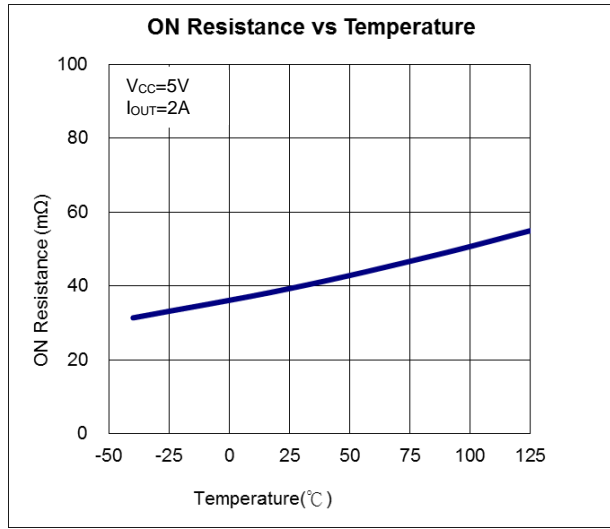
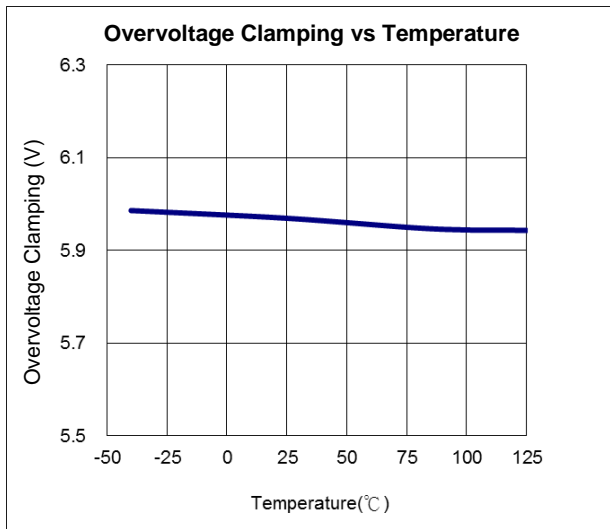
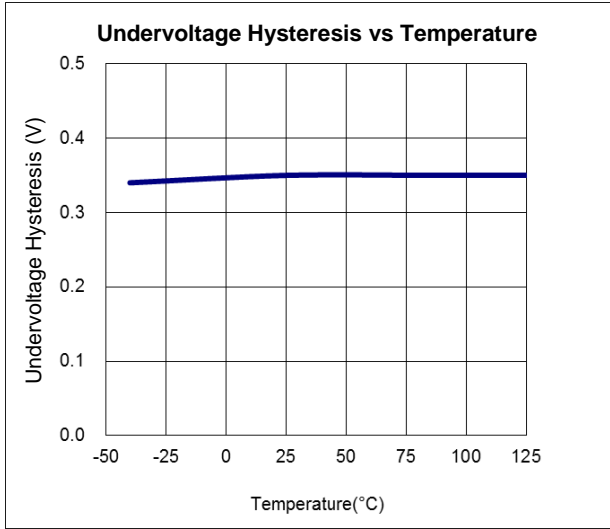
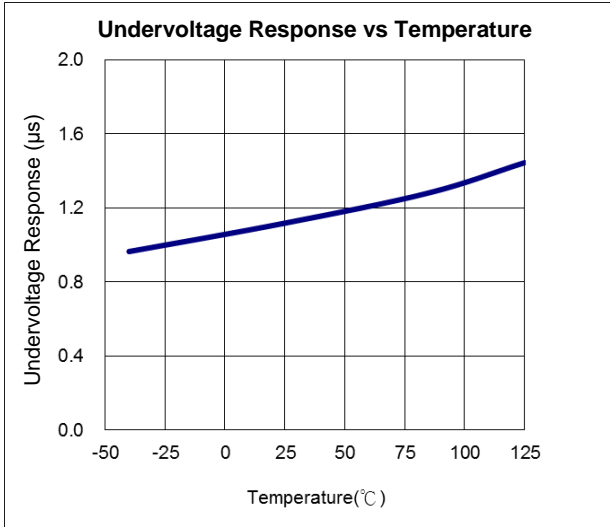
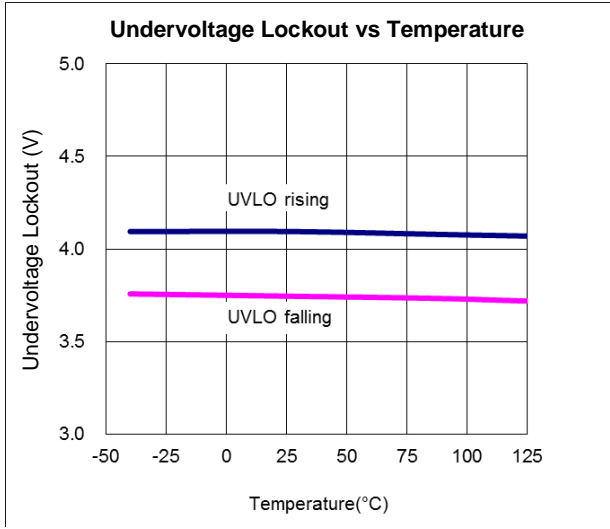
- Notes:
- Typical data is measured at T<sub>A</sub> = +25°C, V<sub>CC</sub> = 5V. The maximum and minimum parameters values over operating temperature range are not tested in production, they are guaranteed by design, characterization and process control.
  - The slew rate control is held in reset until the input voltage is greater than the UVLO rising threshold and Enable = High. The slew rate control is reset when input voltage drops below UVLO falling threshold, Enable changes from High to Mid or Low, SA = High or reverse current detection.
  - Reverse current detection will latch off the ISOFET switch; In AP91350H, this condition can be reset by undervoltage lockout, by EN/FAULT and SAS pins, or when V<sub>OUT</sub> falls below the supply pin voltage (V<sub>CC</sub>) by 100mV typical at T<sub>A</sub> = +25°C, V<sub>CC</sub> = 5V.

**Electrical Characteristics** (continued) (Note 7) (All specifications are for  $-10^{\circ}\text{C} < T_A < +85^{\circ}\text{C}$ ,  $V_{CC} = 5\text{V}$ , unless otherwise noted.)

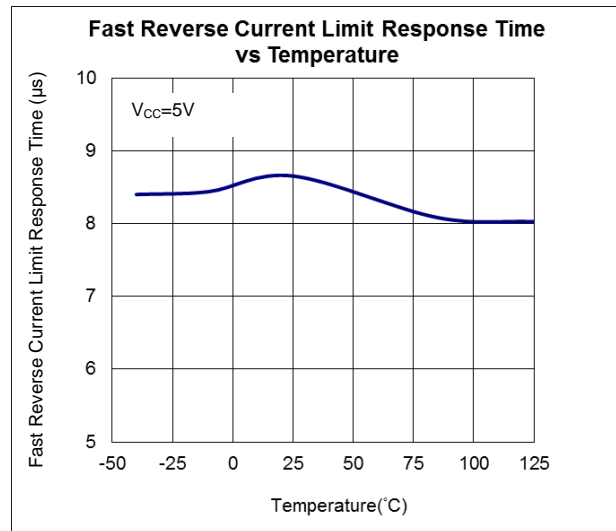
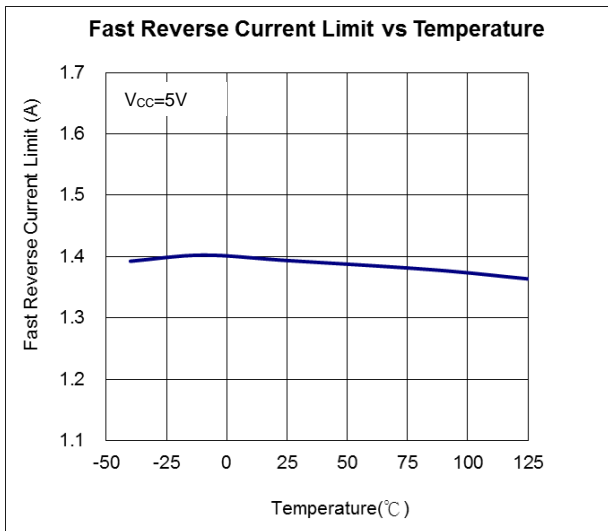
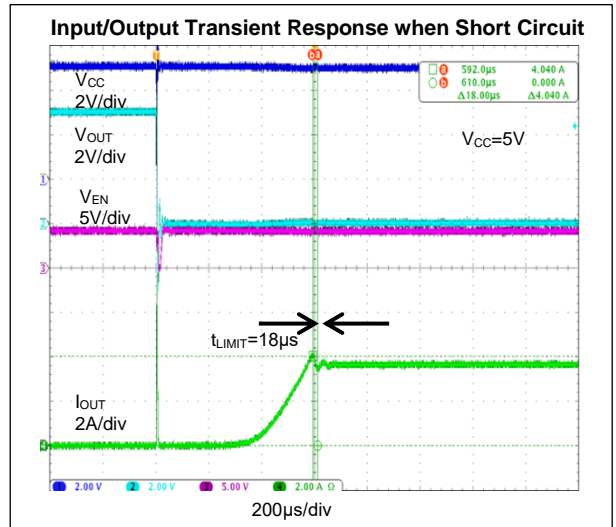
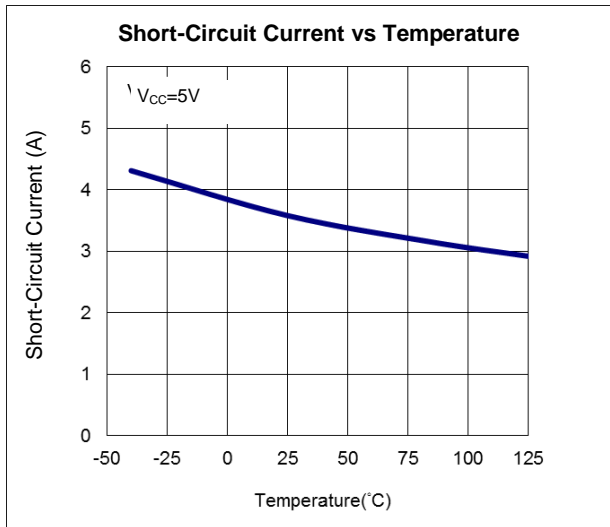
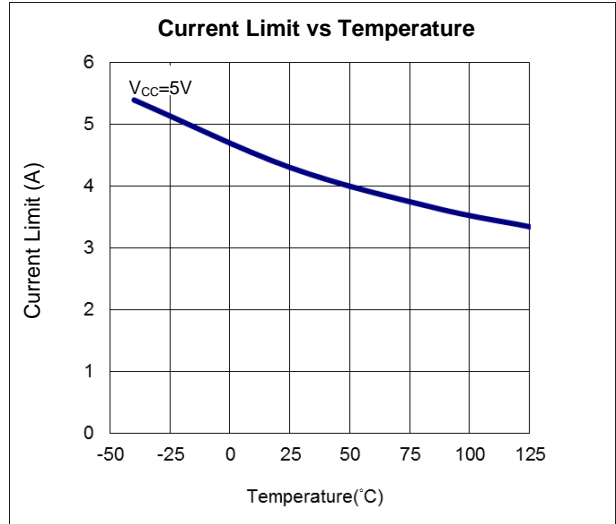
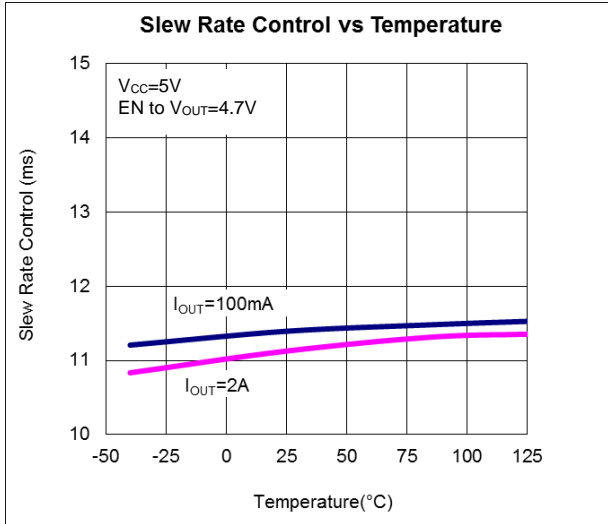
Symbol	Parameters	Conditions	Min	Typ	Max	Unit
<b>SAS Disable</b>						
SAS <sub>L</sub>	Logic Level Low	Output Enabled	0.35	—	1.05	V
SAS <sub>H</sub>	Logic Level High	Output Disabled	1.15	1.4	2.1	V
SAS <sub>Hmax</sub>	Maximum Pin Voltage	—	—	—	3.3	V
SAS- $\Omega$ IN	Input Impedance	To GND	350	500	1000	k $\Omega$
SAS-TDLY	Deglitch Filter	—	2	—	50	$\mu\text{s}$
—	Human Body JESD22-A114	—	1	—	—	kV
—	Charged Device JESD22-C101	—	500	—	—	V

Note: 7. Typical data is measured at  $T_A = +25^{\circ}\text{C}$ ,  $V_{CC} = 5\text{V}$ . The maximum and minimum parameters values over operating temperature range are not tested in production, they are guaranteed by design, characterization and process control.

**Performance Characteristic**



**Performance Characteristic** (continued)



## Application Note

### Theory of Operation

The AP91350H is a self-protected, resettable electronic fuse. It monitors the input and output voltage, the output current and the die temperature. When the AP91350H is powered up, it will ramp up the output voltage based on the fixed slew rate (see *Electrical Characteristics* above) and current will begin to flow. The Overcurrent Protection, Overvoltage Clamp, Undervoltage Lockout and Thermal Protection are internally set.

Also, integrated reverse blocking MOSFET would prevent back-drive from an active load inadvertently causing undetermined behavior in the application.

### Overvoltage Clamping

The AP91350H monitors the input voltage and clamp output voltage once it exceeds 6.25V (max). This will allow for transient on the input for a short period of time. If the input voltage stays above 6.25V (max) for an extended period of time, the voltage drop across the FET with the load current will increase the die temperature and the thermal shutdown feature will protect the device and shut it down.

### Undervoltage Lockout

The input voltage of AP91350H is monitored by a UVLO circuit (undervoltage lockout). If the input voltage drops below this threshold, the output transistor will be pulled into a high impedance state.

### Input Capacitor Selection

The AP91350H is designed to feature multiple fault protections to protect application circuit and device itself. VCC input may have voltage transient upon immediate switch-off behavior by fault events like SCP (Short-Circuit Protection) and OTP (Overtemperature Protection), if excessive voltage transient on VCC is observed, increase capacitance on VCC up to 10μF is recommended.

### Enable/Fault

The AP91350H has a tri-state EN/FAULT pin. It is used to turn on and off the device with high and low signals from a GPIO, but can also indicate a thermal fault. When the EN/FAULT pin is pulled low, the output is turned off; when the EN/FAULT pin is pulled high, the output is turned on. Also, the EN/FAULT pin would be internally pulled high after VCC reaches UVLO. In the event of a thermal fault, the EN/FAULT pin will be pulled low to an intermediate voltage by an internal circuit. This can be used to chain up to 3 eFuses together, like AP91350H, NIS5132 (12V eFuse), or NIS5135 (5V eFuse), so during a thermal shutdown, the linked devices turn off as well.

Due to this fault indication capability, it should not be connected to any type of logic with an internal pullup device.

The AP91350H connected to a 2<sup>nd</sup> device will latch off until the EN/FAULT pin has been pulled to low and then allowed to go back up to a high signal, or SAS pin has been toggled from High to Low or if the power has been cycled. Once the part starts up again, it will go through the start-up ramp determined by the internal circuit, 13ms (typ).

**Table 1. EN/FAULT Signal Levels & Device Status**

Symbol	Description	Enable/Fault	eFuse State	Latching
UVLO	Under Voltage Lock Out	V <sub>L</sub>	Off	No
SAS <sub>H</sub>	SAS Disable = 1	V <sub>L</sub>	Off	N/A
TH <sub>SD</sub>	Thermal Shutdown	V <sub>M</sub>	Off	Yes
I <sub>REVERSE</sub>	Reverse Current Protection	V <sub>M</sub>	Off	(Note 9)
SAS <sub>O</sub>	SAS Disable = Open	V <sub>H</sub>	On	N/A
SAS <sub>L</sub>	SAS Disable = 0	V <sub>H</sub>	On	N/A
—	V <sub>CC</sub> > UVLO, No Fault	V <sub>H</sub>	On	N/A

Note: 9. Reverse current detection will latch off the ISOFET switch; In AP91350H, this condition can be reset by undervoltage lockout, by EN/FAULT and SAS pins, or when V<sub>OUT</sub> falls below the supply pin voltage (V<sub>CC</sub>) by 100mV typical at T<sub>A</sub> = +25°C, V<sub>CC</sub> = 5V.

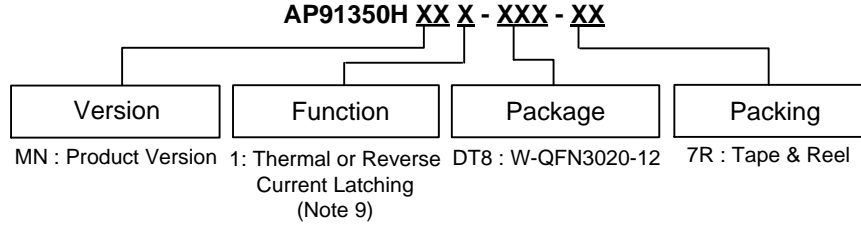
### Thermal Protection

The AP91350H has an integrated temperature sensing circuit that protects the die in the event of overtemperature. The trip point has been intentionally set high at +150°C (typ) to allow for increased trip times during high power transient events. The AP91350H will shut down current flow to the output when the die temperature reaches +150°C (typ). The AP91350H will restart after the Enable pin has been toggled or the input power has been cycled.

Even though the thermal trip point has been set high to allow for high current transients, the circuit design should accomplish best thermal performance with good thermal layout of the PCB. It is not recommended to operate AP91350H above +150°C over extended period of time.



**Ordering Information**



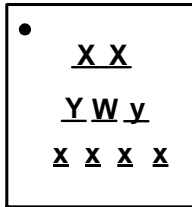
Part Number	Part Number Suffix	Package Code	Package (Note 10)	Packing	
				Qty.	Carrier
AP91350HMN1-DT8-7R	-7R	DT8	W-QFN3020-12	3000	Tape & Reel

Notes: 9. Reverse current detection will latch off the ISOFET switch; In AP91350H, this condition can be reset by undervoltage lockout, by EN/FAULT and SAS pins, or when  $V_{OUT}$  falls below the supply pin voltage ( $V_{CC}$ ) by 100mV typical at  $T_A = +25^\circ\text{C}$ ,  $V_{CC} = 5\text{V}$ .  
 10. Pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at <http://www.diodes.com/package-outlines.html>.

**Marking Information**

W-QFN3020-12

( Top View )



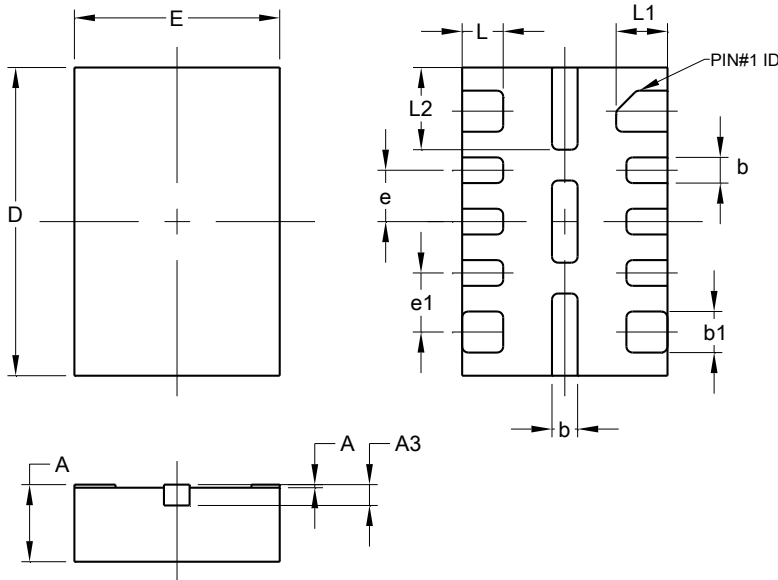
- XX : Identification Code
- Y : Year : 0 to 9 (ex: 4 = 2024)
- W : Week : A to Z : week 1 to 26; a to z : week 27 to 52; z represents week 52 and 53
- y : Internal Code
- x : Internal Code

Part Number	Package	Identification Code
AP91350HMN1-DT8-7R	W-QFN3020-12	H9

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

W-QFN3020-12

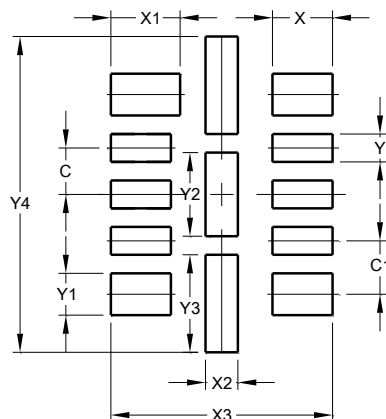


W-QFN3020-12			
Dim	Min	Max	Typ
A	0.700	0.800	-
A1	0	0.05	-
A3	0.203REF		
b	0.200	0.300	-
b1	0.350	0.450	-
D	1.900	2.100	2.000
E	2.900	3.100	3.000
e	-	-	0.500
e1	-	-	0.575
L	0.350	0.450	-
L1	0.450	0.550	-
L2	0.750	0.850	-
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

W-QFN3020-12



Dimensions	Value (in mm)
C	0.500
G	0.575
X	0.650
X1	0.750
X2	0.350
X3	2.400
Y	0.300
Y1	0.450
Y2	0.900
Y3	1.050
Y4	3.400

## Mechanical Data

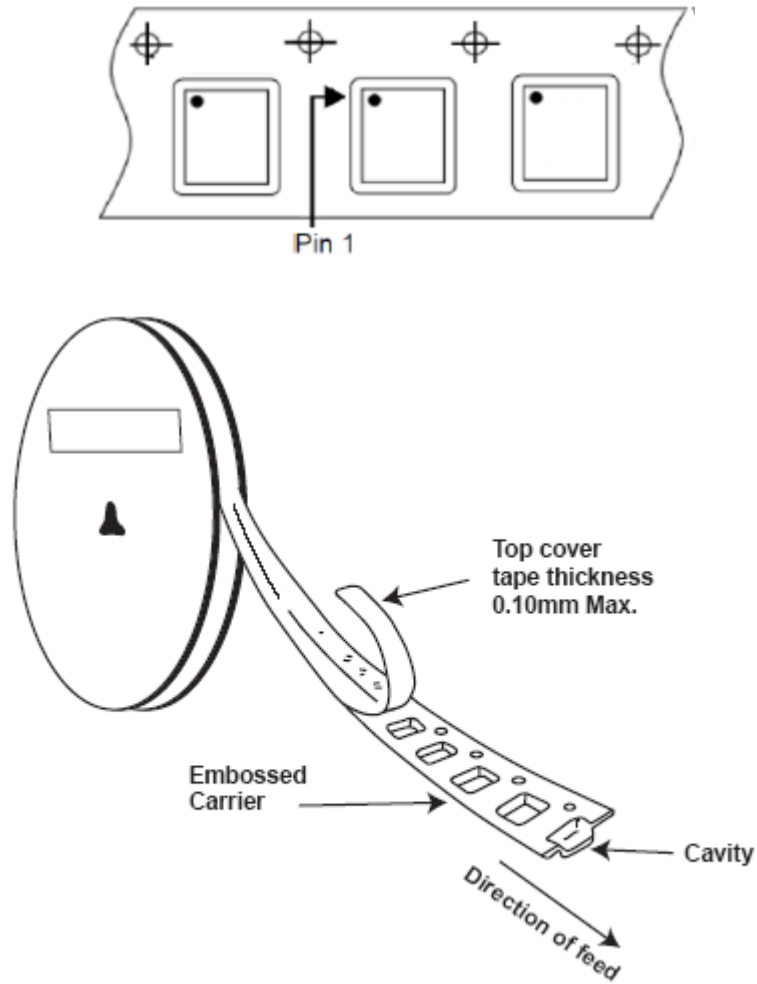
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish-Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.012 grams (Approximate)

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## Taping Orientation

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Package Type: W-QFN3020-12



Note: 11. The taping orientation of the other package type can be found on our website at <https://www.diodes.com/assets/Packaging-Support-Docs/ap02007.pdf>.

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